Z80®-CPU
Z80A-CPU

Product Specification

MARCH 1978

The Zilog Z80 product line is a complete set of microcomputer components, development systems and support software. The Z80 microcomputer component set includes all of the circuits necessary to build high-performance microcomputer systems with virtually no other logic and a minimum number of low cost standard memory elements.

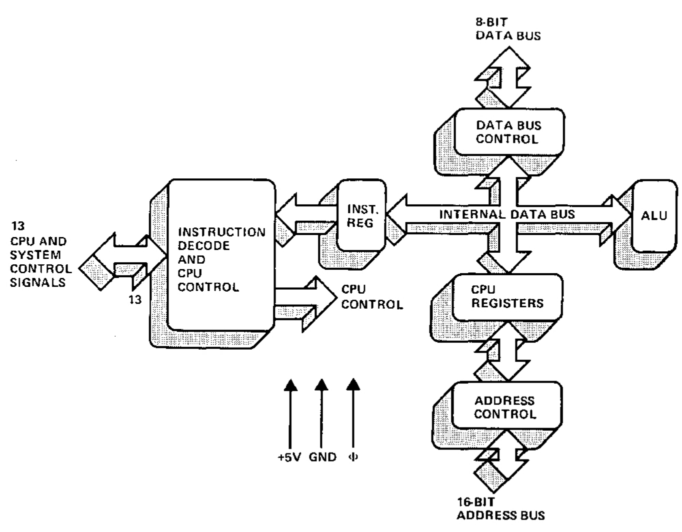
The Z80 and Z80A CPU's are third generation single chip microprocessors with unrivaled computational power. This increased computational power results in higher system through-put and more efficient memory utilization when compared to second generation microprocessors. In addition, the Z80 and Z80A CPU's are very easy to implement into a system because of their single voltage requirement plus all output signals are fully decoded and timed to control standard memory or peripheral circuits. The circuit is implemented using an N-channel, ion implanted, silicon gate MOS process.

Figure 1 is a block diagram of the CPU, Figure 2 details the internal register configuration which contains 208 bits of Read/Write memory that are accessible to the programmer. The registers include two sets of six general purpose registers that may be used individually as 8-bit registers or as 16-bit register pairs. There are also two sets of accumulator and flag registers. The programmer has access to either set of main or alternate registers through a group of exchange instructions. This alternate set allows foreground/background mode of operation or may be reserved for very fast Interrupt response. Each CPU also contains a 16-bit stack pointer which permits simple implementation of multiple level interrupts, unlimited subroutine nesting and simplification of many types of data handling.

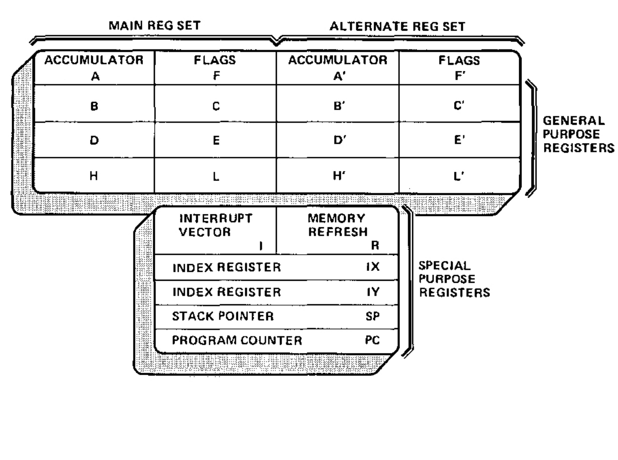
The two 16-bit index registers allow tabular data manipulation and easy implementation of relocatable code. The Refresh register provides for automatic, totally transparent refresh of external dynamic memories. The I register is used in a powerful interrupt response mode to form the upper 8 bits of a pointer to a interrupt service address table, while the interrupting device supplies the lower 8 bits of the pointer. An indirect call is then made to this service address.

FEATURES

- Single chip, N-channel Silicon Gate CPU.
- 158 instructions–includes all 78 of the 8080A instructions with total software compatibility. New instructions include 4-, 8- and 16-bit operations with more useful addressing modes such as indexed, bit and relative.
- 17 internal registers.
- Three modes of fast interrupt response plus a non-maskable interrupt.
- Directly interfaces standard speed static or dynamic memories with virtually no external logic.
- 1.0 μs instruction execution speed.
- Single 5 VDC supply and single-phase 5 volt Clock.
- Out-performs any other single chip microcomputer in 4-, 8-, or 16-bit applications.
- All pins TTL Compatible
- Built-in dynamic RAM refresh circuitry.

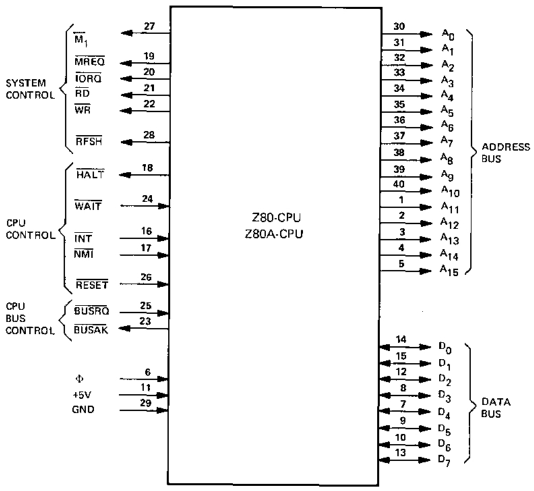


Z80, Z80A CPU BLOCK DIAGRAM



Z80, Z80A CPU REGISTERS

Z80, Z80A-CPU Pin Description



Z80, Z80A CPU PIN CONFIGURATION

A_0-A_{15} (Address Bus)
: Tri-state output, active high. A_0-A_{15} constitute a 16-bit address bus. The address bus provides the address for memory (up to 64K bytes) data exchanges and for I/O device data exchanges.

D_0-D_7 (Data Bus)
: Tri-state input/output, active high. D_0 - D_7 constitute an 8-bit bidirectional data bus. The data bus is used for data exchanges with memory and I/O devices.

$\overline{M_1}$ (Machine Cycle one)
: Output, active low. $\overline{M_1}$ indicates that the current machine cycle is the OP code fetch cycle of an instruction execution.

$\overline{\text{MREQ}}$ (Memory Request)
: Tri-state output, active low. The memory request signal indicates that the address bus holds a valid address for a memory read or memory write operation.

$\overline{\text{IORQ}}$ (Input/Output Request)
: Tri-state output, active low. The $\overline{\text{IORQ}}$ signal indicates that the lower half of the address bus holds a valid I/O address for a I/O read or write operation. An $\overline{\text{IORQ}}$ signal is also generated when an interrupt is being acknowledged to indicate that an interrupt response vector can be placed on the data bus.

$\overline{\text{RD}}$ (Memory Read)
: Tri-state output, active low. $\overline{\text{RD}}$ indicates that the CPU wants to read data from memory or an I/O device. The addressed I/O device or memory should use this signal to gate data onto the CPU data bus.

$\overline{\text{WR}}$ (Memory Write)
: Tri-state output, active low. $\overline{\text{WR}}$ indicates that the CPU data bus holds valid data to be stored in the addressed memory or I/O device.

$\overline{\text{RFSH}}$ (Refresh)
: Output, active low. $\overline{\text{RFSH}}$ indicates that the lower 7 bits of the address bus contain a refresh address for dynamic memories and the current $\overline{\text{MREQ}}$ signal should be used to do a refresh read to all dynamic memories.

$\overline{\text{HALT}}$ (Halt state)
: Output, active low. $\overline{\text{HALT}}$ indicates that the CPU has executed a HALT software instruction and is awaiting either a non-maskable or a maskable interrupt (with the mask enabled) before operation can resume. While halted, the CPU executes NOP's to maintain memory refresh activity.

$\overline{\text{WAIT}}$ (Wait)
: Input, active low. $\overline{\text{WAIT}}$ indicates to the Z-80 CPU that the addressed memory or I/O devices are not ready for a data transfer. The CPU continues to enter wait states for as long as this signal is active.

$\overline{\text{INT}}$ (Interrupt Request)
: Input, active low. The Interrupt Request signal is generated by I/O devices. A request will be honored at the end of the current instruction if the internal software controlled interrupt enable flip-flop (IFF) is enabled.

$\overline{\text{NMI}}$ (Non Maskable Interrupt)
: Input, active low. The non-maskable nterrupt request line has a higher priority than $\overline{\text{INT}}$ and is always recognized at the end of the current instruction, independent of the status of the interrupt enable flip-flop. $\overline{\text{NMI}}$ automatically forces the Z-80 CPU to restart to location 0066_H.

$\overline{\text{RESET}}$
: Input, active low. $\overline{\text{RESET}}$ initializes the CPU as follows: reset interrupt enable flip-flop, clear PC and registers I and R and set interrupt to 8080A mode. During reset time, the address and data bus go to a high impedance state and all control output signals go to the inactive state.

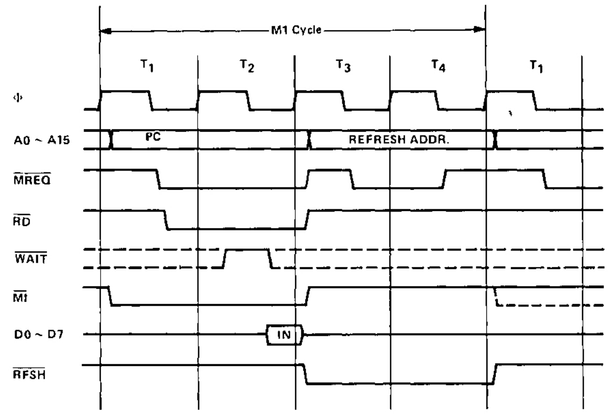
$\overline{\text{BUSRQ}}$ (Bus Request)
: Input, active low. The bus request signal has a higher priority than $\overline{\text{NMI}}$ and is always recognized at the end of the current machine cycle and is used to request the CPU address bus, data bus and tri-state output control signals to go to a high impedance state so that other devices can control these busses.

$\overline{\text{BUSAK}}$ (Bus Acknowledge)
: Output, active low. Bus acknowledge is used to indicate to the requesting device that the CPU address bus, data bus and tri-state control bus signals have been set to their high impedance state and the external device can now control these signals.

Timing Waveforms

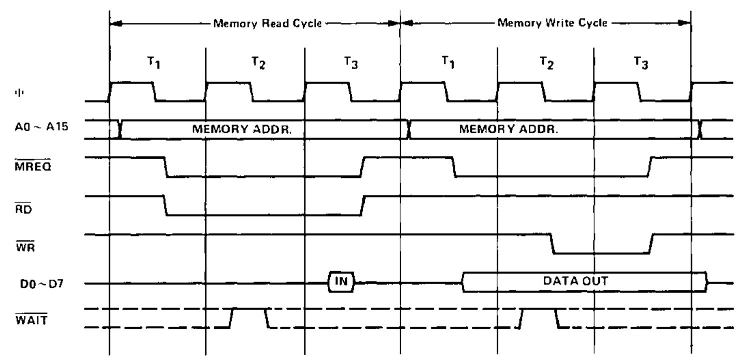
INSTRUCTION OP CODE FETCH

The program counter content (PC) is placed on the address bus immediately at the start of the cycle. One half clock time later $\overline{MREQ}$ goes active. The falling edge of $\overline{MREQ}$ can be used directly as a chip enable to dynamic memories. $\overline{RD}$ when active indicates that the memory data should be enabled onto the CPU data bus. The CPU samples data with the rising edge of the clock state T_3. Clock states T_3 and T_4 of a fetch cycle are used to refresh dynamic memories while the CPU is internally decoding and executing the instruction. The refresh control signal $\overline{RFSH}$ indicates that a refresh read of all dynamic memories should be accomplished.



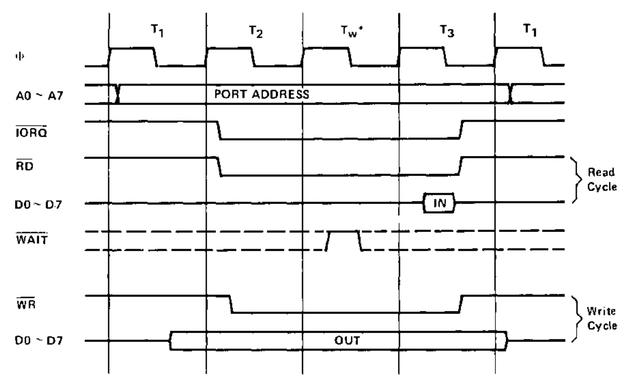
MEMORY READ OR WRITE CYCLES

Illustrated here is the timing of memory read or write cycles other than an OP code fetch (M_1 cycle). The $\overline{MREQ}$ and $\overline{RD}$ signals are used exactly as in the fetch cycle. In the case of a memory write cycle, the $\overline{MREQ}$ also becomes active when the address bus is stable so that it can be used directly as a chip enable for dynamic memories. The $\overline{WR}$ line is active when data on the data bus is stable so that it can be used directly as a R/W pulse to virtually any type of semiconductor memory.



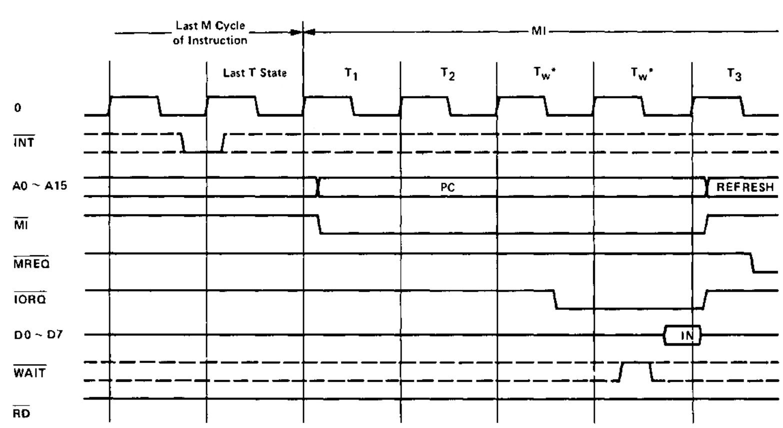
INPUT OR OUTPUT CYCLES

Illustrated here is the timing for an I/O read or I/O write operation. Notice that during I/O operations a single wait state is automatically inserted (Tw*). The reason for this is that during I/O operations this extra state allows sufficient time for an I/O port to decode its address and activate the $\overline{WAIT}$ line if a wait is required.



INTERRUPT REQUEST/ACKNOWLEDGE CYCLE

The interrupt signal is sampled by the CPU with the rising edge of the last clock at the end of any instruction. When an interrupt is accepted, a special M_1 cycle is generated. During this M_1 cycle, the $\overline{IORQ}$ signal becomes active (instead of $\overline{MREQ}$) to indicate that the interrupting device can place an 8-bit vector on the data bus. Two wait states (Tw*) are automatically added to this cycle so that a ripple priority interrupt scheme, such as the one used in the Z80 peripheral controllers, can be easily implemented.



Z80, Z80A Instruction Set

The following is a summary of the Z80, Z80A instruction set showing the assembly language mnemonic and the symbolic operation performed by the instruction. A more detailed listing appears in the Z80-CPU technical manual, and assembly language programming manual. The instructions are divided into the following categories:

8-bit loads	Miscellaneous Group
16-bit loads	Rotates and Shifts
Exchanges	Bit Set, Reset and Test
Memory Block Moves	Input and Output
Memory Block Searches	Jumps
8-bit arithmetic and logic	Calls
16-bit arithmetic	Restarts
General purpose Accumulator & Flag Operations	Returns

In the table the following terminology is used.

- b ≡ a bit number in any 8-bit register or memory location
- cc ≡ flag condition code
  - NZ ≡ non zero
  - Z ≡ zero
  - NC ≡ non carry
  - C ≡ carry
  - PO ≡ Parity odd or no over flow
  - PE ≡ Parity even or over flow
  - P ≡ Positive
  - M ≡ Negative (minus)
- d ≡ any 8-bit destination register or memory location
- dd ≡ any 16-bit destination register or memory location
- e ≡ 8-bit signed 2's complement displacement used in relative jumps and indexed addressing
- L ≡ 8 special call locations in page zero. In decimal notation these are 0, 8, 16, 24, 32, 40, 48 and 56
- n ≡ any 8-bit binary number
- nn ≡ any 16-bit binary number
- r ≡ any 8-bit general purpose register (A, B, C, D, E, H, or L)
- s ≡ any 8-bit source register or memory location
- s_b ≡ a bit in a specific 8-bit register or memory location
- ss ≡ any 16-bit source register or memory location
- subscript "L" ≡ the low order 8 bits of a 16-bit register
- subscript "H" ≡ the high order 8 bits of a 16-bit register
- ( ) ≡ the contents within the ( ) are to be used as a pointer to a memory location or I/O port number

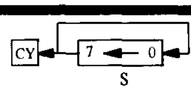
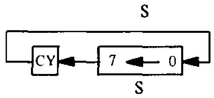
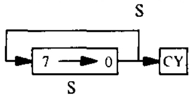
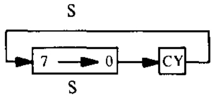
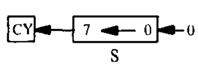
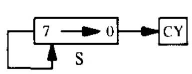
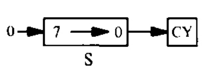
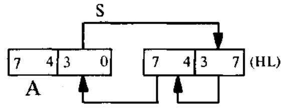
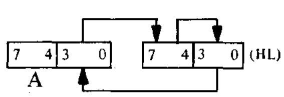
8-bit registers are A, B, C, D, E, H, L, I and R
16-bit register pairs are AF, BC, DE and HL
16-bit registers are SP, PC, IX and IY

Addressing Modes implemented include combinations of the following:

Immediate	Indexed
Immediate extended	Register
Modified Page Zero	Implied
Relative	Register Indirect
Extended	Bit

	Mnemonic	Symbolic Operation	Comments
8-BIT LOADS	LD r, s	r ← s	s ≡ r, n, (HL), (IX+e), (IY+e)
	LD d, r	d ← r	d ≡ (HL), r (IX+e), (IY+e)
	LD d, n	d ← n	d ≡ (HL), (IX+e), (IY+e)
	LD A, s	A ← s	s ≡ (BC), (DE), (nn), I, R
	LD d, A	d ← A	d ≡ (BC), (DE), (nn), I, R
16-BIT LOADS	LD dd, nn	dd ← nn	dd ≡ BC, DE, HL, SP, IX, IY
	LD dd, (nn)	dd ← (nn)	dd ≡ BC, DE, HL, SP, IX, IY
	LD (nn), ss	(nn) ← ss	ss ≡ BC, DE, HL, SP, IX, IY
	LD SP, ss	SP ← ss	ss = HL, IX, IY
	PUSH ss	$(SP-1) \leftarrow ss_H; (SP-2) \leftarrow ss_L$	ss = BC, DE, HL, AF, IX, IY
	POP dd	$dd_L \leftarrow (SP); dd_H \leftarrow (SP+1)$	dd = BC, DE, HL, AF, IX, IY
EXCHANGES	EX DE, HL	DE ↔ HL	
	EX AF, AF′	AF ↔ AF′	
	EXX	(BC, DE, HL) ↔ (BC′, DE′, HL′)	
	EX (SP), ss	$(SP) \leftrightarrow ss_L, (SP+1) \leftrightarrow ss_H$	ss ≡ HL, IX, IY

	Mnemonic	Symbolic Operation	Comments
MEMORY BLOCK MOVES	LDI	(DE) ← (HL), DE ← DE+1 HL ← HL+1, BC ← BC-1	
	LDIR	(DE) ← (HL), DE ← DE+1 HL ← HL+1, BC ← BC-1 Repeat until BC = 0	
	LDD	(DE) ← (HL), DE ← DE-1 HL ← HL-1, BC ← BC-1	
	LDDR	(DE) ← (HL), DE ← DE-1 HL ← HL-1, BC ← BC-1 Repeat until BC = 0	
MEMORY BLOCK SEARCHES	CPI	A-(HL), HL ← HL+1 BC ← BC-1	
	CPIR	A-(HL), HL ← HL+1 BC ← BC-1, Repeat until BC = 0 or A = (HL)	A-(HL) sets the flags only. A is not affected
	CPD	A-(HL), HL ← HL-1 BC ← BC-1	
	CPDR	A-(HL), HL ← HL-1 BC ← BC-1, Repeat until BC= 0 or A = (HL)	
8-BIT ALU	ADD s	A ← A + s	
	ADC s	A ← A + s + CY	CY is the carry flag
	SUB s	A ← A - s	
	SBC s	A ← A - s - CY	s ≡ r, n, (HL) (IX+e), (IY+e)
	AND s	A ← A ∧ s	
	OR s	A ← A ∨ s	
	XOR s	A ← A ⊕ s	

Group	Mnemonic	Symbolic Operation	Comments
8-BIT ALU	CP s	A - s	s = r, n (HL) (IX+e), (IY+e)
	INC d	d ← d + 1	d = r, (HL) (IX+e), (IY+e)
	DEC d	d ← d - 1	
16-BIT ARITHMETIC	ADD HL, ss	HL ← HL + ss	ss ≡ BC, DE HL, SP
	ADC HL, ss	HL ← HL + ss + CY	
	SBC HL, ss	HL ← HL - ss - CY	
	ADD IX, ss	IX ← IX + ss	ss ≡ BC, DE, IX, SP
	ADD IY, ss	IY ← IY + ss	ss ≡ BC, DE, IY, SP
	INC dd	dd ← dd + 1	dd ≡ BC, DE, HL, SP, IX, IY
	DEC dd	dd ← dd - 1	dd ≡ BC, DE, HL, SP, IX, IY
GP ACC. & FLAG	DAA	Converts A contents into packed BCD following add or subtract.	Operands must be in packed BCD format
	CPL	$A \leftarrow \overline{A}$	
	NEG	A ← 00 – A	
	CCF	$CY \leftarrow \overline{CY}$	
	SCF	CY ← 1	
MISCELLANEOUS	NOP	No operation	
	HALT	Halt CPU	
	DI	Disable Interrupts	
	EI	Enable Interrupts	
	IM 0	Set interrupt mode 0	8080A mode
	IM 1	Set interrupt mode 1	Call to 0038_H
	IM 2	Set interrupt mode 2	Indirect Call
ROTATES AND SHIFTS	RLC s		s ≡ r, (HL) (IX+e), (IY+e)
	RL s		
	RRC s		
	RR s		
	SLA s		
	SRA s		
	SRL s		
	RLD		
	RRD		

Group	Mnemonic	Symbolic Operation	Comments
BIT S, R, & T	BIT b, s	$Z \leftarrow \overline{s_b}$	Z is zero flag s ≡ r, (HL) (IX+e), (IY+e)
	SET b, s	$s_b \leftarrow 1$	
	RES b, s	$s_b \leftarrow 0$	
INPUT AND OUTPUT	IN A, (n)	A ← (n)	
	IN r, (C)	r ← (C)	Set flags
	INI	(HL) ← (C), HL ← HL + 1 B ← B - 1	
	INIR	(HL) ← (C), HL ← HL + 1 B ← B - 1 Repeat until B = 0	
	IND	(HL) ← (C), HL ← HL - 1 B ← B - 1	
	INDR	(HL) ← (C), HL ← HL - 1 B ← B - 1 Repeat until B = 0	
	OUT(n), A	(n) ← A	
	OUT(C), r	(C) ← r	
	OUTI	(C) ← (HL), HL ← HL + 1 B ← B - 1	
	OTIR	(C) ← (HL), HL ← HL + 1 B ← B - 1 Repeat until B = 0	
	OUTD	(C) ← (HL), HL ← HL - 1 B ← B - 1	
	OTDR	(C) ← (HL), HL ← HL - 1 B ← B - 1 Repeat until B = 0	
JUMPS	JP nn	PC ← nn	cc { NZ PO, Z PE, NC P, C M
	JP cc, nn	If condition cc is true PC ← nn, else continue	
	JR e	PC ← PC + e	
	JR kk, e	If condition kk is true PC ← PC + e, else continue	kk { NZ NC, Z C
	JP (ss)	PC ← ss	ss = HL, IX, IY
	DJNZ e	B ← B - 1, if B = 0 continue, else PC ← PC + e	
CALLS	CALL nn	(SP-1) ← PC_H (SP-2) ← PC_L, PC ← nn	cc { NZ PO, Z PE, NC P, C M
	CALL cc, nn	If condition cc is false continue, else same as CALL nn	
RESTARTS	RST L	(SP-1) ← PC_H (SP-2) ← PC_L, PC_H ← 0 PC_L ← L	
RETURNS	RET	PC_L ← (SP), PC_H ← (SP+1)	
	RET cc	If condition cc is false continue, else same as RET	cc { NZ PO, Z PE, NC P, C M
	RETI	Return from interrupt, same as RET	
	RETN	Return from non-maskable interrupt	

T_A = 0°C to 70°C, Vcc = +5V ± 5%, Unless Otherwise Noted.

Signal	Symbol	Parameter	Min	Max	Unit	Test Condition
Φ	t_c	Clock Period	.4	[12]	µsec	
	$t_w(\Phi H)$	Clock Pulse Width, Clock High	180	[E]	nsec	
	$t_w(\Phi L)$	Clock Pulse Width, Clock Low	180	2000	nsec	
	$t_{r,f}$	Clock Rise and Fall Time		30	nsec	
A_{0-15}	$t_{D(AD)}$	Address Output Delay		145	nsec	C_L = 50pF
	$t_{F(AD)}$	Delay to Float		110	nsec	
	t_{acm}	Address Stable Prior to $\overline{MREQ}$ (Memory Cycle)	[1]		nsec	
	t_{aci}	Address Stable Prior to $\overline{IORQ}$, $\overline{RD}$ or $\overline{WR}$ (I/O Cycle)	[2]		nsec	
	t_{ca}	Address Stable from $\overline{RD}$, $\overline{WR}$, $\overline{IORQ}$ or $\overline{MREQ}$	[3]		nsec	
	t_{caf}	Address Stable From $\overline{RD}$ or $\overline{WR}$ During Float	[4]		nsec	
D_{0-7}	$t_{D(D)}$	Data Output Delay		230	nsec	C_L = 50pF
	$t_{F(D)}$	Delay to Float During Write Cycle		90	nsec	
	$t_{S\Phi(D)}$	Data Setup Time to Rising Edge of Clock During M1 Cycle	50		nsec	
	$t_{S\overline{\Phi}(D)}$	Data Setup Time to Falling Edge of Clock During M2 to M5	60		nsec	
	t_{dcm}	Data Stable Prior to $\overline{WR}$ (Memory Cycle)	[5]		nsec	
	t_{dci}	Data Stable Prior to $\overline{WR}$ (I/O Cycle)	[6]		nsec	
	t_{cdf}	Data Stable From $\overline{WR}$	[7]			
	t_H	Any Hold Time for Setup Time	0		nsec	
$\overline{MREQ}$	$t_{DL\overline{\Phi}(MR)}$	$\overline{MREQ}$ Delay From Falling Edge of Clock, $\overline{MREQ}$ Low		100	nsec	C_L = 50pF
	$t_{DH\Phi(MR)}$	$\overline{MREQ}$ Delay From Rising Edge of Clock, $\overline{MREQ}$ High		100	nsec	
	$t_{DH\overline{\Phi}(MR)}$	$\overline{MREQ}$ Delay From Falling Edge of Clock, $\overline{MREQ}$ High		100	nsec	
	$t_{w(\overline{MRL})}$	Pulse Width, $\overline{MREQ}$ Low	[8]		nsec	
	$t_{w(\overline{MRH})}$	Pulse Width, $\overline{MREQ}$ High	[9]		nsec	
$\overline{IORQ}$	$t_{DL\Phi(IR)}$	$\overline{IORQ}$ Delay From Rising Edge of Clock, $\overline{IORQ}$ Low		90	nsec	C_L = 50pF
	$t_{DL\overline{\Phi}(IR)}$	$\overline{IORQ}$ Delay From Falling Edge of Clock, $\overline{IORQ}$ Low		110	nsec	
	$t_{DH\Phi(IR)}$	$\overline{IORQ}$ Delay From Rising Edge of Clock, $\overline{IORQ}$ High		100	nsec	
	$t_{DH\overline{\Phi}(IR)}$	$\overline{IORQ}$ Delay From Falling Edge of Clock, $\overline{IORQ}$ High		110	nsec	
$\overline{RD}$	$t_{DL\Phi(RD)}$	$\overline{RD}$ Delay From Rising Edge of Clock, $\overline{RD}$ Low		100	nsec	C_L = 50pF
	$t_{DL\overline{\Phi}(RD)}$	$\overline{RD}$ Delay From Falling Edge of Clock, $\overline{RD}$ Low		130	nsec	
	$t_{DH\Phi(RD)}$	$\overline{RD}$ Delay From Rising Edge of Clock, $\overline{RD}$ High		100	nsec	
	$t_{DH\overline{\Phi}(RD)}$	$\overline{RD}$ Delay From Falling Edge of Clock, $\overline{RD}$ High		110	nsec	
$\overline{WR}$	$t_{DL\Phi(WR)}$	$\overline{WR}$ Delay From Rising Edge of Clock, $\overline{WR}$ Low		80	nsec	C_L = 50pF
	$t_{DL\overline{\Phi}(WR)}$	$\overline{WR}$ Delay From Falling Edge of Clock, $\overline{WR}$ Low		90	nsec	
	$t_{DH\overline{\Phi}(WR)}$	$\overline{WR}$ Delay From Falling Edge of Clock, $\overline{WR}$ High		100	nsec	
	$t_{w(\overline{WRL})}$	Pulse Width, $\overline{WR}$ Low	[10]		nsec	
$\overline{M1}$	$t_{DL(M1)}$	$\overline{M1}$ Delay From Rising Edge of Clock, $\overline{M1}$ Low		130	nsec	C_L = 50pF
	$t_{DH(M1)}$	$\overline{M1}$ Delay From Rising Edge of Clock, $\overline{M1}$ High		130	nsec	
$\overline{RFSH}$	$t_{DL(RF)}$	$\overline{RFSH}$ Delay From Rising Edge of Clock, $\overline{RFSH}$ Low		180	nsec	C_L = 50pF
	$t_{DH(RF)}$	$\overline{RFSH}$ Delay From Rising Edge of Clock, $\overline{RFSH}$ High		150	nsec	
$\overline{WAIT}$	$t_{s(WT)}$	$\overline{WAIT}$ Setup Time to Falling Edge of Clock	70		nsec	
$\overline{HALT}$	$t_{D(HT)}$	$\overline{HALT}$ Delay Time From Falling Edge of Clock		300	nsec	C_L = 50pF
$\overline{INT}$	$t_{s(IT)}$	$\overline{INT}$ Setup Time to Rising Edge of Clock	80		nsec	
$\overline{NMI}$	$t_{w(\overline{NML})}$	Pulse Width, $\overline{NMI}$ Low	80		nsec	
$\overline{BUSRQ}$	$t_{s(BQ)}$	$\overline{BUSRQ}$ Setup Time to Rising Edge of Clock	80		nsec	
$\overline{BUSAK}$	$t_{DL(BA)}$	$\overline{BUSAK}$ Delay From Rising Edge of Clock, $\overline{BUSAK}$ Low		120	nsec	C_L = 50pF
	$t_{DH(BA)}$	$\overline{BUSAK}$ Delay From Falling Edge of Clock, $\overline{BUSAK}$ High		110	nsec	
$\overline{RESET}$	$t_{s(RS)}$	$\overline{RESET}$ Setup Time to Rising Edge of Clock	90		nsec	
	$t_{F(C)}$	Delay to Float ($\overline{MREQ}$, $\overline{IORQ}$, $\overline{RD}$ and $\overline{WR}$)		100	nsec	
	t_{mr}	$\overline{M1}$ Stable Prior to $\overline{IORQ}$ (Interrupt Ack.)	[11]		nsec	

[12] $t_c = t_{w(\Phi H)} + t_{w(\Phi L)} + t_r + t_f$

[1] $t_{acm} = t_{w(\Phi H)} + t_f - 75$

[2] $t_{aci} = t_c - 80$

[3] $t_{ca} = t_{w(\Phi L)} + t_r - 40$

[4] $t_{caf} = t_{w(\Phi L)} + t_r - 60$

[5] $t_{dcm} = t_c - 210$

[6] $t_{dci} = t_{w(\Phi L)} + t_r - 210$

[7] $t_{cdf} = t_{w(\Phi L)} + t_r - 80$

[8] $t_{w(MRL)} = t_c - 40$

[9] $t_{w(MRH)} = t_{w(\Phi H)} + t_f - 30$

[10] $t_{w(\overline{WRL})} = t_c - 40$

[11] $t_{mr} = 2t_c + t_{w(\Phi H)} + t_f - 80$

NOTES:

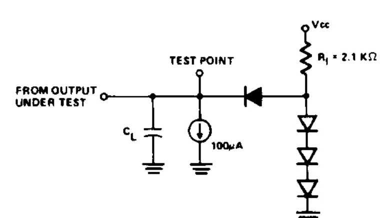
A. Data should be enabled onto the CPU data bus when $\overline{RD}$ is active. During interrupt acknowledge data should be enabled when $\overline{M1}$ and $\overline{IORQ}$ are both active.

B. All control signals are internally synchronized, so they may be totally asynchronous with respect to the clock.

C. The $\overline{RESET}$ signal must be active for a minimum of 3 clock cycles.

D. Output Delay vs. Loaded Capacitance
TA = 70°C Vcc = +5V ±5%
Add 10nsec delay for each 50pf increase in load up to a maximum of 200pf for the data bus & 100pf for address & control lines

E. Although static by design, testing guarantees $t_{w(\Phi H)}$ of 200 µsec maximum

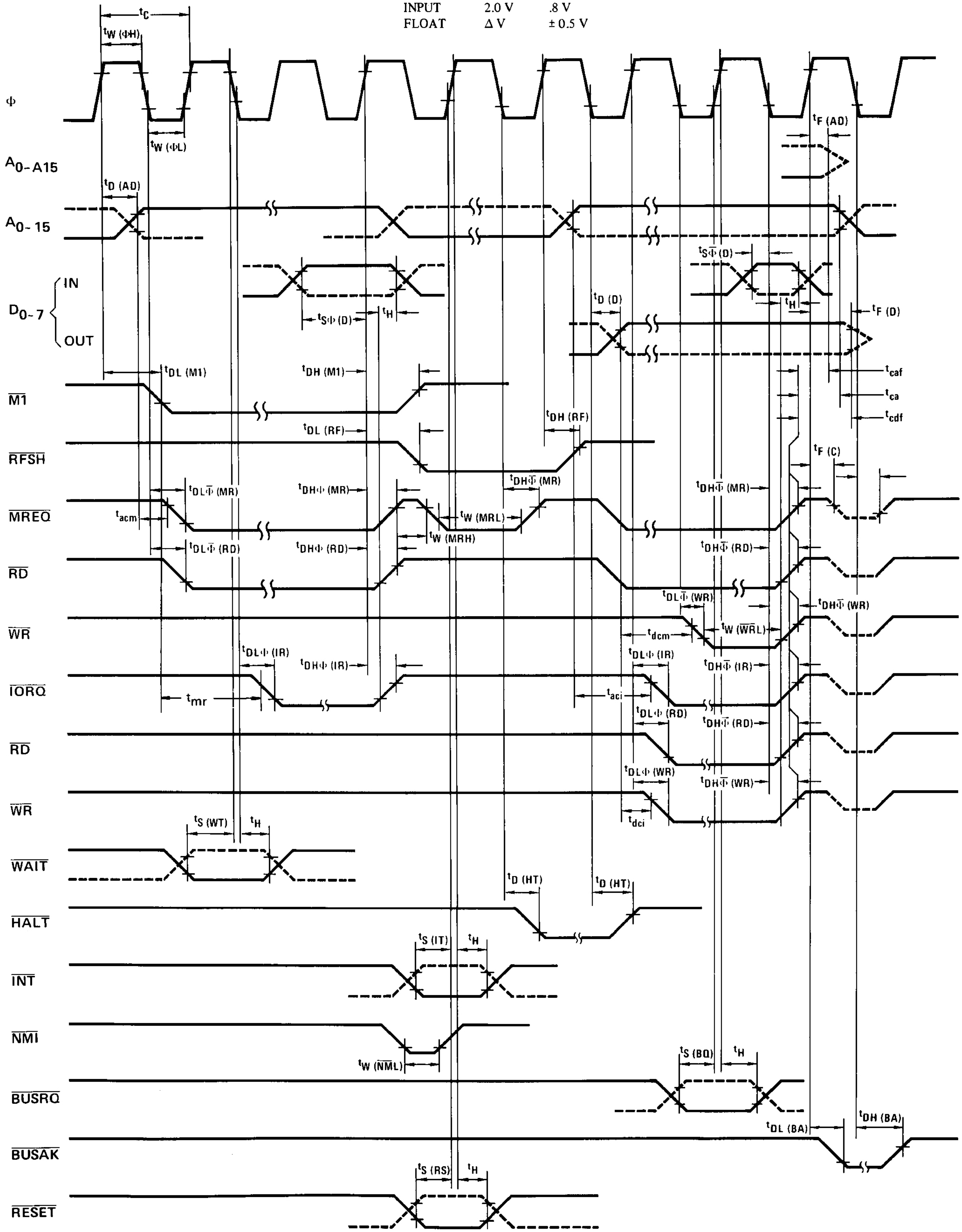


Load circuit for Output

A.C. Timing Diagram

Timing measurements are made at the following voltages, unless otherwise specified:

	"1"	"0"
CLOCK	V_{cc} -.6V	.45V
OUTPUT	2.0 V	.8 V
INPUT	2.0 V	.8 V
FLOAT	Δ V	± 0.5 V



Absolute Maximum Ratings

Temperature Under Bias	Specified operating range.
Storage Temperature	-65°C to +150°C
Voltage On Any Pin with Respect to Ground	-0.3V to +7V
Power Dissipation	1.5W

*Comment

Stresses above those listed under "Absolute Maximum Rating" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other condition above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Note: For Z80-CPU all AC and DC characteristics remain the same for the military grade parts except I_{cc}.

I_{cc} = 200 mA

Z80-CPU D.C. Characteristics

T_A = 0°C to 70°C, V_{cc} = 5V ± 5% unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	-0.3		0.45	V	
V_{IHC}	Clock Input High Voltage	V_{cc} -.6		V_{cc}+.3	V	
V_{IL}	Input Low Voltage	-0.3		0.8	V	
V_{IH}	Input High Voltage	2.0		V_{cc}	V	
V_{OL}	Output Low Voltage			0.4	V	I_{OL}=1.8mA
V_{OH}	Output High Voltage	2.4			V	I_{OH} = -250μA
I_{CC}	Power Supply Current			150	mA	
I_{LI}	Input Leakage Current			10	μA	V_{IN}=0 to V_{cc}
I_{LOH}	Tri-State Output Leakage Current in Float			10	μA	V_{OUT}=2.4 to V_{cc}
I_{LOL}	Tri-State Output Leakage Current in Float			-10	μA	V_{OUT}=0.4V
I_{LD}	Data Bus Leakage Current in Input Mode			±10	μA	$0 \leq V_{IN} \leq V_{cc}$

Capacitance

T_A = 25°C, f = 1 MHz,
unmeasured pins returned to ground

Symbol	Parameter	Max.	Unit
C_Φ	Clock Capacitance	35	pF
C_{IN}	Input Capacitance	5	pF
C_{OUT}	Output Capacitance	10	pF

Z80-CPU Ordering Information

C – Ceramic
P – Plastic
S – Standard 5V ±5% 0° to 70°C
E – Extended 5V ±5% -40° to 85°C
M – Military 5V ±10% -55° to 125°C

Z80A-CPU D.C. Characteristics

T_A = 0°C to 70°C V_{cc} = 5V ± 5% unless otherwise specified

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Condition
V_{ILC}	Clock Input Low Voltage	-0.3		0.45	V	
V_{IHC}	Clock Input High Voltage	V_{cc} -.6		V_{cc}+.3	V	
V_{IL}	Input Low Voltage	-0.3		0.8	V	
V_{IH}	Input High Voltage	2.0		V_{cc}	V	
V_{OL}	Output Low Voltage			0.4	V	I_{OL}=1.8mA
V_{OH}	Output High Voltage	2.4			V	I_{OH} = -250μA
I_{CC}	Power Supply Current		90	200	mA	
I_{LI}	Input Leakage Current			10	μA	V_{IN}=0 to V_{cc}
I_{LOH}	Tri-State Output Leakage Current in Float			10	μA	V_{OUT}=2.4 to V_{cc}
I_{LOL}	Tri-State Output Leakage Current in Float			-10	μA	V_{OUT}=0.4V
I_{LD}	Data Bus Leakage Current in Input Mode			±10	μA	$0 \leq V_{IN} \leq V_{cc}$

Capacitance

T_A = 25°C, f = 1 MHz,
unmeasured pins returned to ground

Symbol	Parameter	Max.	Unit
C_Φ	Clock Capacitance	35	pF
C_{IN}	Input Capacitance	5	pF
C_{OUT}	Output Capacitance	10	pF

Z80A-CPU Ordering Information

C – Ceramic
P – Plastic
S – Standard 5V ±5% 0° to 70°C

$T_A = 0°C$ to $70°C$, $V_{cc} = +5V \pm 5\%$, Unless Otherwise Noted.

Signal	Symbol	Parameter	Min	Max	Unit	Test Condition
Φ	t_c	Clock Period	.25	[12]	μsec	
	$t_w(\Phi H)$	Clock Pulse Width, Clock High	110	[E]	nsec	
	$t_w(\Phi L)$	Clock Pulse Width, Clock Low	110	2000	nsec	
	$t_{r,f}$	Clock Rise and Fall Time		30	nsec	
A_{0-15}	$t_{D(AD)}$	Address Output Delay		110	nsec	$C_L = 50pF$
	$t_{F(AD)}$	Delay to Float		90	nsec	
	t_{acm}	Address Stable Prior to $\overline{MREQ}$ (Memory Cycle)	[1]		nsec	
	t_{aci}	Address Stable Prior to $\overline{IORQ}$, $\overline{RD}$ or $\overline{WR}$ (I/O Cycle)	[2]		nsec	
	t_{ca}	Address Stable from $\overline{RD}$, $\overline{WR}$, $\overline{IORQ}$ or $\overline{MREQ}$	[3]		nsec	
	t_{caf}	Address Stable From $\overline{RD}$ or $\overline{WR}$ During Float	[4]		nsec	
D_{0-7}	$t_{D(D)}$	Data Output Delay		150	nsec	$C_L = 50pF$
	$t_{F(D)}$	Delay to Float During Write Cycle		90	nsec	
	$t_{S\Phi(D)}$	Data Setup Time to Rising Edge of Clock During M1 Cycle	35		nsec	
	$t_{S\overline{\Phi}(D)}$	Data Setup Time to Falling Edge of Clock During M2 to M5	50		nsec	
	t_{dcm}	Data Stable Prior to $\overline{WR}$ (Memory Cycle)	[5]		nsec	
	t_{dci}	Data Stable Prior to $\overline{WR}$ (I/O Cycle)	[6]		nsec	
	t_{cdf}	Data Stable From $\overline{WR}$	[7]			
	t_H	Any Hold Time for Setup Time		0	nsec	
$\overline{MREQ}$	$t_{DL\overline{\Phi}(MR)}$	$\overline{MREQ}$ Delay From Falling Edge of Clock, $\overline{MREQ}$ Low		85	nsec	$C_L = 50pF$
	$t_{DH\Phi(MR)}$	$\overline{MREQ}$ Delay From Rising Edge of Clock, $\overline{MREQ}$ High		85	nsec	
	$t_{DH\overline{\Phi}(MR)}$	$\overline{MREQ}$ Delay From Falling Edge of Clock, $\overline{MREQ}$ High		85	nsec	
	$t_{w(\overline{MRL})}$	Pulse Width, $\overline{MREQ}$ Low	[8]		nsec	
	$t_{w(\overline{MRH})}$	Pulse Width, $\overline{MREQ}$ High	[9]		nsec	
$\overline{IORQ}$	$t_{DL\Phi(IR)}$	$\overline{IORQ}$ Delay From Rising Edge of Clock, $\overline{IORQ}$ Low		75	nsec	$C_L = 50pF$
	$t_{DL\overline{\Phi}(IR)}$	$\overline{IORQ}$ Delay From Falling Edge of Clock, $\overline{IORQ}$ Low		85	nsec	
	$t_{DH\Phi(IR)}$	$\overline{IORQ}$ Delay From Rising Edge of Clock, $\overline{IORQ}$ High		85	nsec	
	$t_{DH\overline{\Phi}(IR)}$	$\overline{IORQ}$ Delay From Falling Edge of Clock, $\overline{IORQ}$ High		85	nsec	
$\overline{RD}$	$t_{DL\Phi(RD)}$	$\overline{RD}$ Delay From Rising Edge of Clock, $\overline{RD}$ Low		85	nsec	$C_L = 50pF$
	$t_{DL\overline{\Phi}(RD)}$	$\overline{RD}$ Delay From Falling Edge of Clock, $\overline{RD}$ Low		95	nsec	
	$t_{DH\Phi(RD)}$	$\overline{RD}$ Delay From Rising Edge of Clock, $\overline{RD}$ High		85	nsec	
	$t_{DH\overline{\Phi}(RD)}$	$\overline{RD}$ Delay From Falling Edge of Clock, $\overline{RD}$ High		85	nsec	
$\overline{WR}$	$t_{DL\Phi(WR)}$	$\overline{WR}$ Delay From Rising Edge of Clock, $\overline{WR}$ Low		65	nsec	$C_L = 50pF$
	$t_{DL\overline{\Phi}(WR)}$	$\overline{WR}$ Delay From Falling Edge of Clock, $\overline{WR}$ Low		80	nsec	
	$t_{DH\overline{\Phi}(WR)}$	$\overline{WR}$ Delay From Falling Edge of Clock, $\overline{WR}$ High		80	nsec	
	$t_{w(\overline{WRL})}$	Pulse Width, $\overline{WR}$ Low	[10]		nsec	
$\overline{M1}$	$t_{DL(M1)}$	$\overline{M1}$ Delay From Rising Edge of Clock, $\overline{M1}$ Low		100	nsec	$C_L = 50pF$
	$t_{DH(M1)}$	$\overline{M1}$ Delay From Rising Edge of Clock, $\overline{M1}$ High		100	nsec	
$\overline{RFSH}$	$t_{DL(RF)}$	$\overline{RFSH}$ Delay From Rising Edge of Clock, $\overline{RFSH}$ Low		130	nsec	$C_L = 50pF$
	$t_{DH(RF)}$	$\overline{RFSH}$ Delay From Rising Edge of Clock, $\overline{RFSH}$ High		120	nsec	
$\overline{WAIT}$	$t_{s(WT)}$	$\overline{WAIT}$ Setup Time to Falling Edge of Clock	70		nsec	
$\overline{HALT}$	$t_{D(HT)}$	$\overline{HALT}$ Delay Time From Falling Edge of Clock		300	nsec	$C_L = 50pF$
$\overline{INT}$	$t_{s(IT)}$	$\overline{INT}$ Setup Time to Rising Edge of Clock	80		nsec	
$\overline{NMI}$	$t_{w(\overline{NML})}$	Pulse Width, $\overline{NMI}$ Low	80		nsec	
$\overline{BUSRQ}$	$t_{s(BQ)}$	$\overline{BUSRQ}$ Setup Time to Rising Edge of Clock	50		nsec	
$\overline{BUSAK}$	$t_{DL(BA)}$	$\overline{BUSAK}$ Delay From Rising Edge of Clock, $\overline{BUSAK}$ Low		100	nsec	$C_L = 50pF$
	$t_{DH(BA)}$	$\overline{BUSAK}$ Delay From Falling Edge of Clock, $\overline{BUSAK}$ High		100	nsec	
$\overline{RESET}$	$t_{s(RS)}$	$\overline{RESET}$ Setup Time to Rising Edge of Clock	60		nsec	
	$t_{F(C)}$	Delay to Float ($\overline{MREQ}$, $\overline{IORQ}$, $\overline{RD}$ and $\overline{WR}$)		80	nsec	
	t_{mr}	M1 Stable Prior to IORQ (Interrupt Ack.)	[11]		nsec	

[12] $t_c = t_{w(\Phi H)} + t_{w(\Phi L)} + t_r + t_f$

[1] $t_{acm} = t_{w(\Phi H)} + t_f - 65$

[2] $t_{aci} = t_c - 70$

[3] $t_{ca} = t_{w(\Phi L)} + t_r - 50$

[4] $t_{caf} = t_{w(\Phi L)} + t_r - 45$

[5] $t_{dcm} = t_c - 170$

[6] $t_{dci} = t_{w(\Phi L)} + t_r - 170$

[7] $t_{cdf} = t_{w(\Phi L)} + t_r - 70$

[8] $t_{w(\overline{MRL})} = t_c - 30$

[9] $t_{w(\overline{MRH})} = t_{w(\Phi H)} + t_f - 20$

[10] $t_{w(\overline{WRL})} = t_c - 30$

[11] $t_{mr} = 2t_c + t_{w(\Phi H)} + t_f - 65$

NOTES:

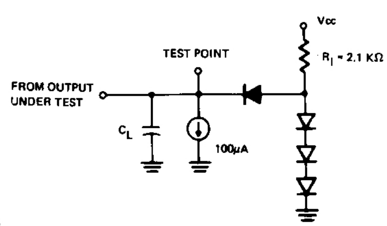
A. Data should be enabled onto the CPU data bus when $\overline{RD}$ is active. During interrupt acknowledge data should be enabled when $\overline{M1}$ and $\overline{IORQ}$ are both active.

B. All control signals are internally synchronized, so they may be totally asynchronous with respect to the clock.

C. The $\overline{RESET}$ signal must be active for a minimum of 3 clock cycles.

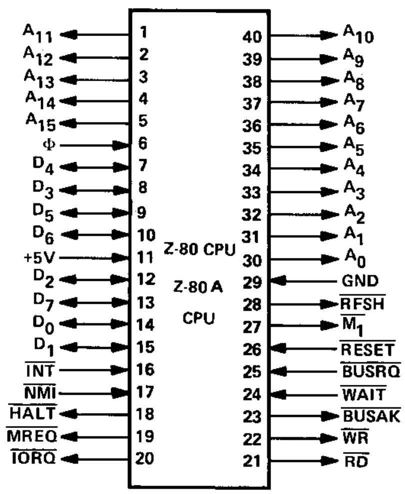
D. Output Delay vs. Loaded Capacitance
TA = 70°C Vcc = +5V ±5%
Add 10nsec delay for each 50pf increase in load up to maximum of 200pf for data bus and 100pf for address & control lines.

E. Although static by design, testing guarantees $t_{w(\Phi H)}$ of 200 μsec maximum

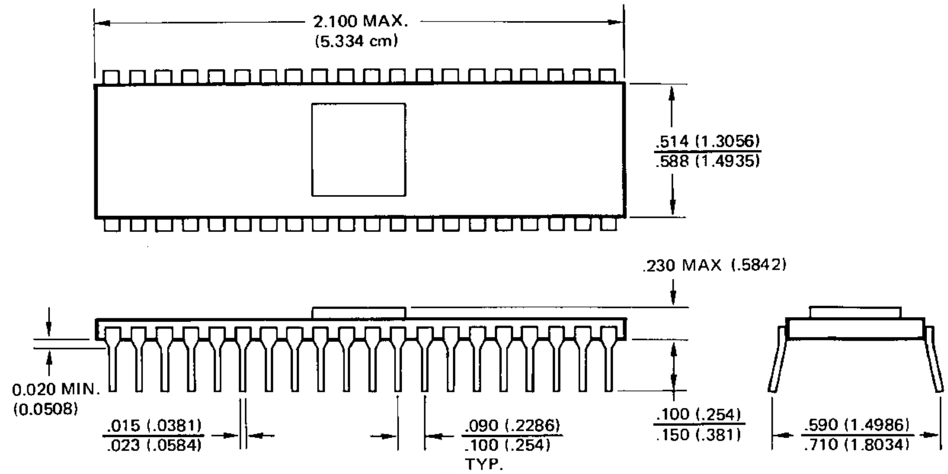


Load circuit for Output

Package Configuration



Package Outline



*Dimensions for metric system are in parentheses